

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-137 (Canceled)

Claim 138 (Previously Presented): A liquid crystal display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film over said thin film transistor;
a common electrode having a function of a black matrix over said first interlayer insulating film;
a second interlayer insulating film over said common electrode;
a pixel line and at least one pixel electrode both formed over the second interlayer insulating film, said pixel electrode extending from said pixel line; and
a liquid crystal layer over said pixel line and said pixel electrode;
wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;
wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and
wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 139 (Previously Presented): A device according to claim 138, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 140 (Previously Presented): A device according to claim 138, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating film.

Claim 141 (Previously Presented): A device according to claim 138, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN, AlN_xO_y, Si₃N₄, and SiO_xN_y.

Claim 142 (Previously Presented): A device according to claim 138, wherein said thin film transistor has a semiconductor layer including a high-resistivity region.

Claim 143 (Previously Presented): A device according to claim 138, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

Claim 144 (Previously Presented): device according to claim 138, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 145 (Previously Presented): A device according to claim 138, wherein said first interlayer insulating film serves as a planarization film.

Claim 146 (Previously Presented): A liquid crystal display device comprising:
a first substrate;
a second substrate opposed to said first substrate;
a thin film transistor over said first substrate;
a first interlayer insulating over said thin film transistor;

a common electrode having a function of a black matrix over said first interlayer insulating;

a second interlayer insulating over said common electrode;

a pixel line and at least one pixel electrode both formed over said second interlayer insulating film, said pixel electrode extending from said pixel line over said second interlayer film; and

a liquid crystal layer over said pixel line and said pixel electrode;

wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;

wherein said liquid crystal layer is driven by an electric field formed between the pixel electrode and the common electrode, the electric field having a component parallel with said first substrate; and

wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 147 (Previously Presented): A device according to claim 146, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 148 (Previously Presented): A device according to claim 146, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating.

Claim 149 (Previously Presented): A device according to claim 146, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

Claim 150 (Previously Presented): A device according to claim 146, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

Claim 151 (Previously Presented): A device according to claim 146, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 152 (Previously Presented): A device according to claim 146, wherein said first interlayer insulating film serves as a planarization film.

Claim 153 (Previously Presented): A liquid crystal display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film comprising an organic resin over said thin film transistor;
a common electrode having a function of a black matrix over said first interlayer insulating film;
a second interlayer insulating film over said common electrode;
a pixel line and at least one pixel electrode both formed over said second interlayer insulating film, said pixel electrode extending from said pixel line; and
a liquid crystal layer over said pixel line and said pixel electrode;
wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;
wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and
wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 154 (Previously Presented): A device according to claim 153, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 155 (Previously Presented): A device according to claim 153, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating film.

Claim 156 (Previously Presented): A device according to claim 153, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN, AlN_xO_y, Si₃N₄, and SiO_xN_y.

Claim 157 (Previously Presented): A device according to claim 153, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm, and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm.

Claim 158 (Previously Presented): A device according to claim 153, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 159 (Previously Presented): A device according to claim 153, wherein said first interlayer insulating film serves as a planarization film.

Claim 160 (Previously Presented): A liquid crystal display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film over said thin film transistor;
a common electrode having a function of a black matrix over said first interlayer insulating film;
a second interlayer insulating film over said common electrode, said second interlayer insulating film comprising at least a first layer comprising an organic resin material and a second layer comprising an inorganic material;

a pixel line and at least one pixel electrode both formed over said second interlayer insulating film, said pixel electrode extending from said pixel line; and
a liquid crystal layer over said pixel line and said pixel electrode;
wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;
wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and
wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 161 (Previously Presented): A device according to claim 160, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 162 (Previously Presented): A device according to claim 160, wherein said second layer of the second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

Claim 163 (Previously Presented): A device according to claim 160, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

Claim 164 (Previously Presented): A device according to claim 160, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 165 (Previously Presented): A device according to claim 160, wherein said first interlayer insulating film serves as a planarization film.

Claim 166 (New): A liquid crystal display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film over said thin film transistor;
a common electrode having a function of a black matrix over said first interlayer insulating film;
a second interlayer insulating film over said common electrode;
a pixel line and a plurality of pixel electrodes both formed over the second interlayer insulating film, said plurality of pixel electrodes extending from said pixel line; and
a liquid crystal layer over said pixel line and said plurality of pixel electrodes;
wherein said plurality of pixel electrodes are electrically connected to the thin film transistor through said pixel line;
wherein said liquid crystal layer is driven by an electric field formed between each of said plurality of pixel electrodes and said common electrode, said electric field having a component parallel with said substrate; and
wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 167 (New): A device according to claim 166, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 168 (New): A device according to claim 166, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating film.

Claim 169 (New): A device according to claim 166, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

Claim 170 (New): A device according to claim 166, wherein said thin film transistor has a semiconductor layer including a high-resistivity region.

Claim 171 (New): A device according to claim 166, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

Claim 172 (New): A device according to claim 166, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 173 (New): A device according to claim 166, wherein said first interlayer insulating film serves as a planarization film.

Claim 174 (New): A device according to claim 166, wherein said first interlayer insulating film serves as a planarization film.

Claim 175 (New): A display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film over said thin film transistor;
a common electrode having a function of a black matrix over said first interlayer insulating film;
a second interlayer insulating film over said common electrode;
a pixel line and a pixel electrode both formed over the second interlayer insulating film, said pixel electrode extending from said pixel line; and
wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line; and
wherein a storage capacitor is formed between said pixel line and said black matrix.

Claim 176 (New): A device according to claim 175, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

Claim 177 (New): A device according to claim 175, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating film.

Claim 178 (New): A device according to claim 175, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

Claim 179 (New): A device according to claim 175, wherein said thin film transistor has a semiconductor layer including a high-resistivity region.

Claim 180 (New): A device according to claim 175, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

Claim 181 (New): A device according to claim 175, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

Claim 182 (New): A device according to claim 175, wherein said first interlayer insulating film serves as a planarization film.

Claim 183 (New): A device according to claim 175, wherein a liquid crystal layer over said pixel line and said pixel electrode; and

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wherein said liquid crystal layer is driven by an electric field formed between each of said pixel electrode and said common electrode, said electric field having a component parallel with said substrate.